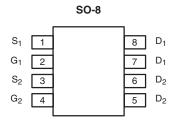


Dual P-Channel 20V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
	0.018 at V _{GS} = - 4.5 V	- 8.9			
- 20	0.022 at V _{GS} = - 2.5 V	- 8.1			
	0.030 at V _{GS} = - 1.8 V	- 3.6			



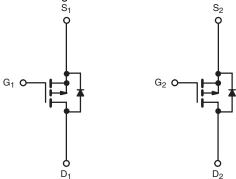
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Advanced High Cell Density Process
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

 Load Switching S₁



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	- 20		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Drain Current /T 150 °C\8	T _A = 25 °C	- I _D	- 8.9	- 6.7	_
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 7.1	- 5.4	
Pulsed Drain Current		I _{DM}	- 30		А
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.7	- 0.9	
M	T _A = 25 °C	P _D	2.0	1.1	W
Maximum Power Dissipation ^a	T _A = 70 °C	1.3	0.7	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R	46	62.5	
	Steady State	R _{thJA}	80	110	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	24	32	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



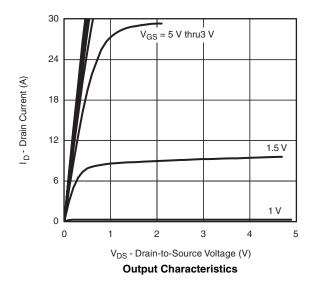
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	<u>'</u>				<u> </u>		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -350 \mu A$	- 0.4		- 1.0	٧	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA	
Zoro Cata Valtaga Drain Current	l	V _{DS} = - 20 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C	V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C		- 5	μΑ	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 30			Α	
		V _{GS} = - 4.5 V, I _D = - 8.9 A		0.018			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 8.1 A		0.022		Ω	
	, ,	V _{GS} = - 1.8 V, I _D = - 3.6 A		0.030			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 8.9 A		26		S	
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.7 A, V _{GS} = 0 V		- 0.7	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			34.5	52		
Gate-Source Charge	Q_{gs}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 8.9 A		5.1		nC	
Gate-Drain Charge	Q_{gd}			9.6		1	
Gate Resistance	R_g			9		Ω	
Turn-On Delay Time	t _{d(on)}			25	40		
se Time t _r		V_{DD} = - 10 V, R_L = 6 Ω		46	70		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		230	345	ns	
Fall Time				155	235		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.7 A, dl/dt = 100 A/μs		128	200		

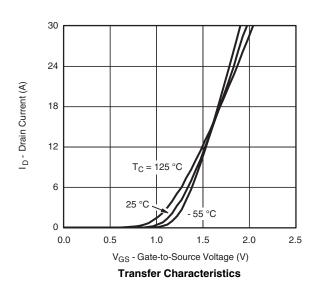
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

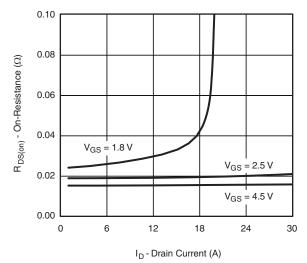
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



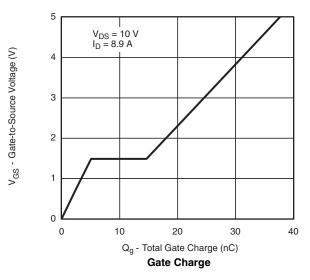


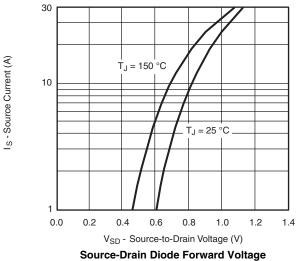


TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



On-Resistance vs. Drain Current



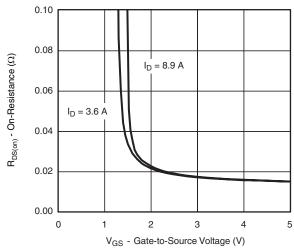


5000 4000 C - Capacitance (pF) C_{iss} 3000 2000 C_{oss} 1000 0 0 2 6 8 10 12 V_{DS} - Drain-to-Source Voltage (V)

Capacitance

1.4 $V_{GS} = 4.5 \text{ V}$ $I_D = 8.9 \text{ A}$ 1.2 R_{DS(on)} - On-Resistance (Normalized) 1.0 0.8 0.6 - 50 - 25 25 150 0 50 75 100 125

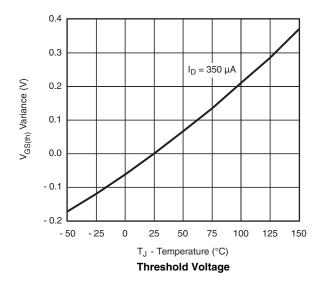
 $\label{eq:TJ} T_J \mbox{ - Junction Temperature (°C)} \\ \mbox{ On-Resistance vs. Junction Temperature }$

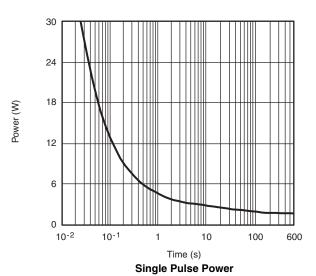


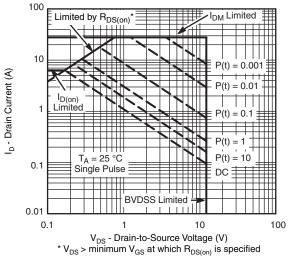
On-Resistance vs. Gate-to-Source Voltage



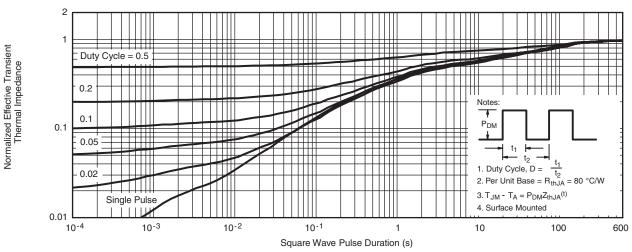
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted







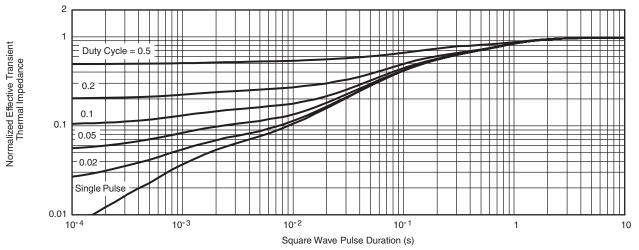




Normalized Thermal Transient Impedance, Junction-to-Ambient



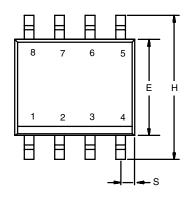
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



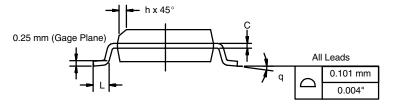
Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEADJEDEC Part Number: MS-012







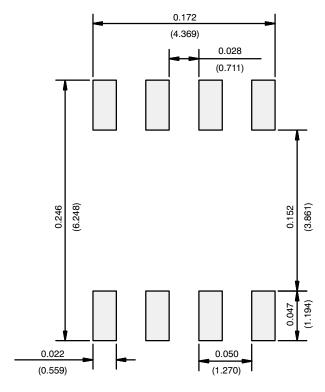
	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06						

DWG: 5498

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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